

SANYO	No.4602A	<h1 style="margin: 0;">2SK2108</h1> <p style="margin: 0;">N-Channel MOS Silicon FET</p> <p style="margin: 0;">Very High-Speed Switching Applications</p>
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Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

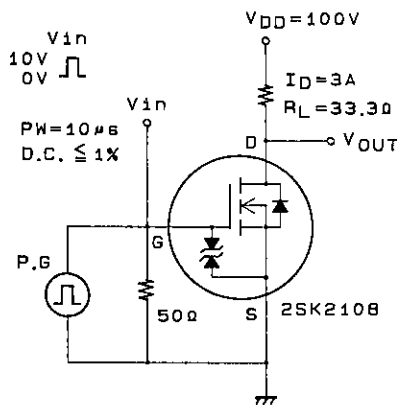
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DSS}	250	V
Gate-to-Source Voltage	V _{GSS}	±30	V
Drain Current(DC)	I _D	6	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	24 A
Allowable Power Dissipation	P _D	Tc = 25°C	2.0 W
			25 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

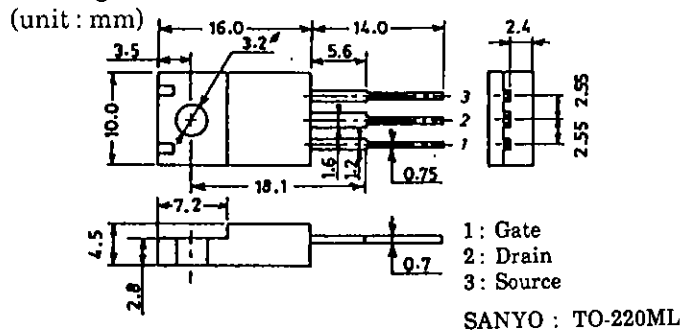
Electrical Characteristics at Ta = 25°C

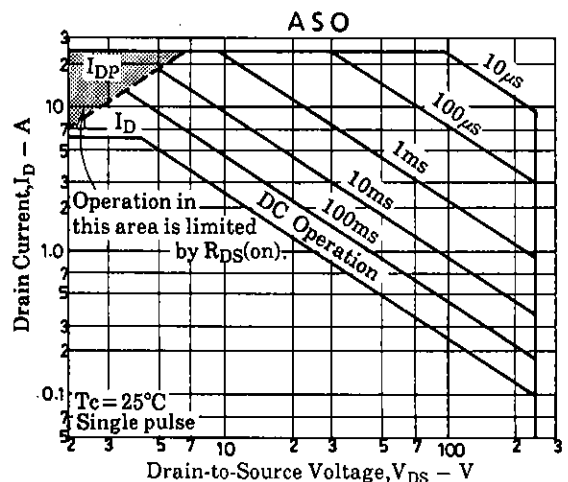
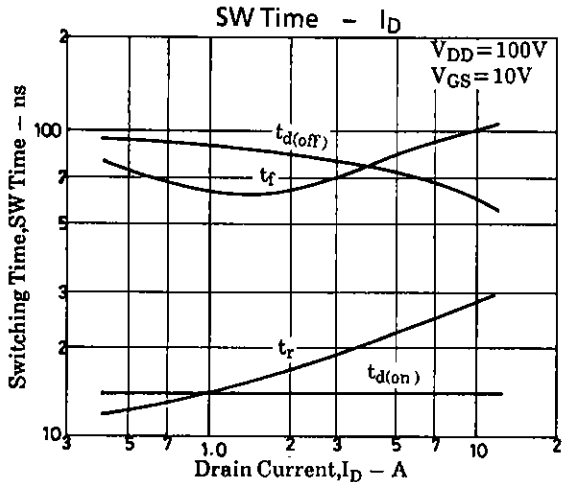
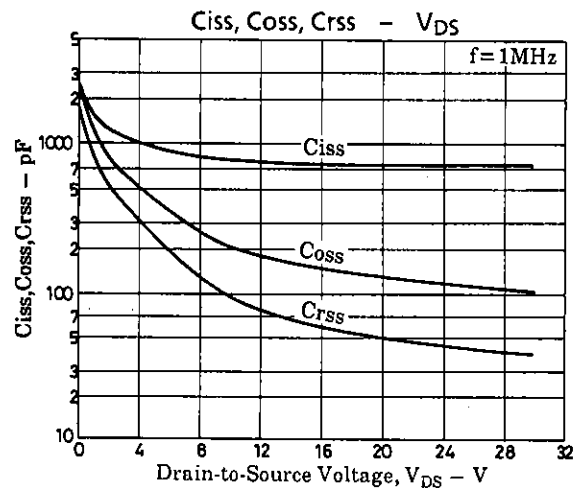
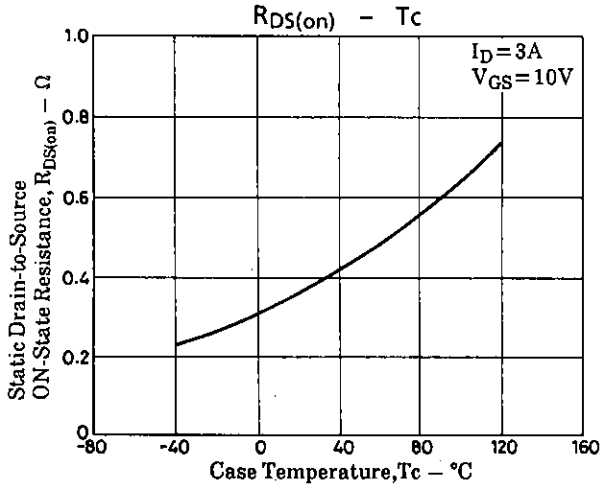
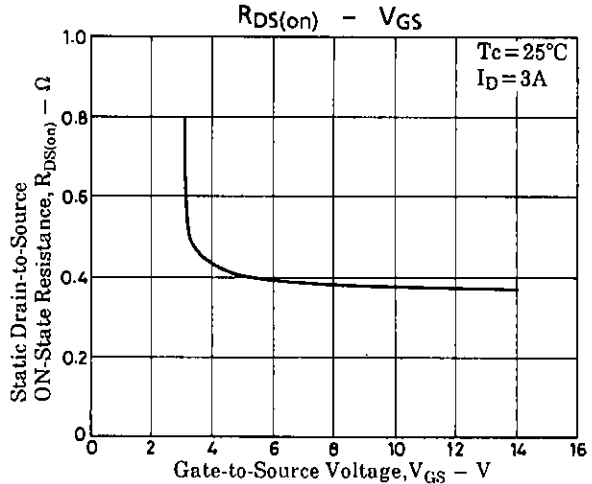
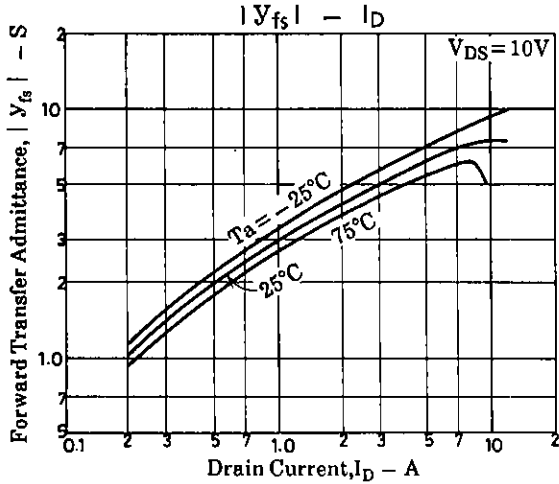
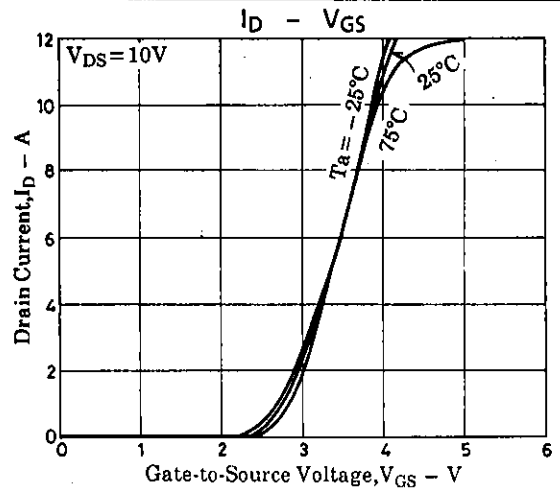
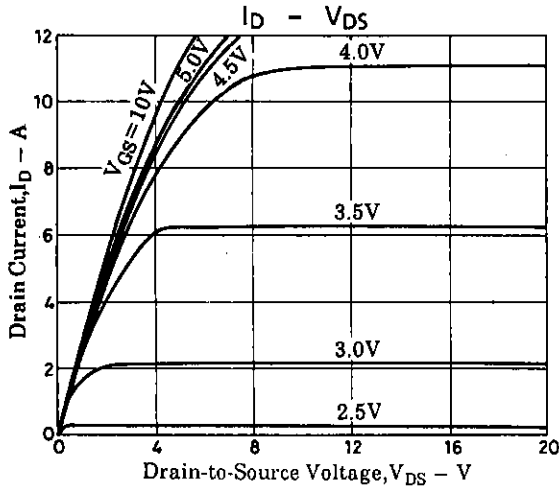
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	250			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 250V, V _{GS} = 0			100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±25V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	1.5		2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, I _D = 3A	3	5		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D = 3A, V _{GS} = 10V	380	500		mΩ
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz		750		pF
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz		130		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz		50		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		14		ns
Rise Time	t _r	"/		19		ns
Turn-OFF Delay Time	t _{d(off)}	"/		80		ns
Fall Time	t _f	"/		70		ns
Diode Forward Voltage	V _{SD}	I _S = 6A, V _{GS} = 0	1.0	1.5		V

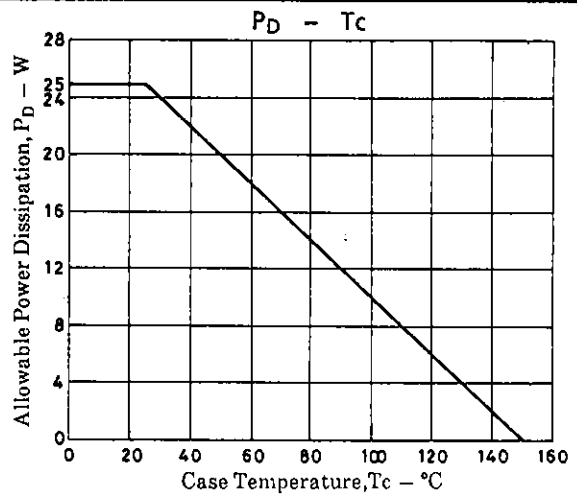
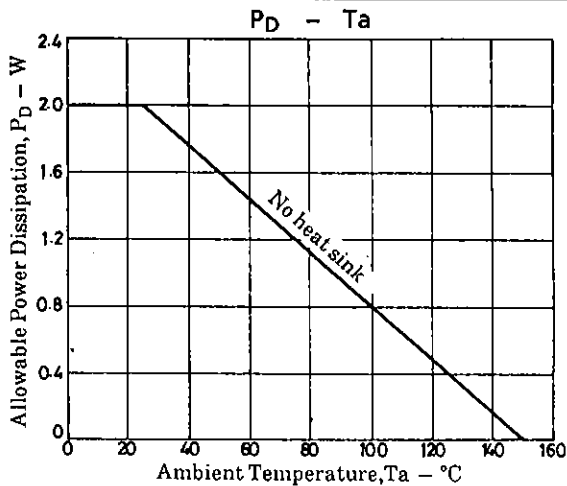
Switching Time Test Circuit



Package Dimensions 2063A







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